

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Priority Application Serial No. 10/280,757
Priority Filing Date October 24, 2002
Inventor Luan C. Tran
Assignee Micron Technology, Inc.
Priority Group Art Unit 2822
Priority Examiner Vu Anh Le
Attorney's Docket No. MI22-2429
Title: A 6F² DRAM Array, A DRAM Array Formed On A Semiconductive Substrate, A
Method Of Forming Memory Cells In A 6F² DRAM Array And A Method Of
Isolating A Single Row Of Memory Cells In A 6F² DRAM Array

INFORMATION DISCLOSURE STATEMENT

References -- See attached Form PTO-1449


In compliance with 37 C.F.R. §§ 1.56, 1.97 and 1.98, your attention is directed to the United States patents and other references listed on the attached Form PTO-1449. No admission is made regarding whether all the submitted references are prior art.

The listed references were cited by, or submitted to, the Office in the parent, co-pending application of the above-identified application. The above-identified application is a divisional application of co-pending application Serial No. 10/280,757, filed October 24, 2002, upon which the above-identified application relies for a priority date under 35 U.S.C. § 120. Such prior disclosure is sufficient for the above-identified application as far as copies of the references are concerned. 37 C.F.R. § 1.98(d) and MPEP § 609(2). As a courtesy, Applicant submits copies of the cited foreign reference and articles (only) for review.

Citation of these references is respectfully requested.

Respectfully submitted,

Dated: Nov. 13, 2003

By: 
Deepak Malhotra
Reg. No. 33,560

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-2429	SERIAL NO. Filed Herewith		
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Luan C. Tran			
				FILING DATE Filed Herewith	GROUP Unassigned		
U.S. PATENT DOCUMENTS							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA	6,175,146 B1	01/16/01	Lane et al.			
	AB	6,165,833	12/26/00	Parekh et al.			
	AC	6,153,899	11/28/00	Ping			
	AD	6,150,211	11/21/00	Zahurak			
	AE	6,141,204	10/31/00	Schuegraf et al.			
	AF	5,994,749	11/30/99	Oda			
	AG	5,972,783	10/26/99	Arai et al.			
	AH	5,960,302	09/28/99	Ma et al.			
	AI	5,880,989	03/09/99	Wilson et al.			
	AJ	5,828,615	10/27/98	Mukunoki et al.			
	AK	5,716,864	02/10/98	Abe			
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation
							Yes No
	AL	WO96/39713	12/12/96	PCT			
	AM						
	AN						
	AO						
	AP						
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
	AR		C.T. Liu et al., <i>Multiple Gate Oxide Thickness for 2GHz System-on-A-Chip Technologies</i> , 1998 IEEE, pages 21.2.1-21.2.4 (4 pages).				
	AS		Lian-Hoon Ko et al., <i>The Effect of Nitrogen Incorporation into the Gate Oxide by Using Shallow Implantation of Nitrogen and Drive-in Process</i> , 1998 IEEE, pages 32-35 (4 pages).				
	AT		Brian Doyle et al., <i>Simultaneous Growth of Different Thickness Gate Oxides in Silicon CMOS Processing</i> , 1995 IEEE, pages 301-302 (2 pages).				
EXAMINER				DATE CONSIDERED			
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Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M122-2429	SERIAL NO. Filed Herewith		
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				FILING DATE Filed Herewith		GROUP Unassigned	
U.S. PATENT DOCUMENTS							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA	5,700,733	12/23/97	Manning			
	AB	5,680,344	10/21/97	Seyyedy			
	AC	5,677,865	10/14/97	Seyyedy			
	AD	5,674,788	10/07/97	Wristers et al.			
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	AF	5,620,908	04/15/97	Inoh et al.			
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	AI	5,254,489	10/19/93	Nakata			
	AJ	5,880,991	3/1999	Hsu et al.			
	AK						
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation
							Yes No
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	AN						
	AO						
	AP						
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
	AR		T. Kuroi et al., <i>The Effects of Nitrogen Implantation Into P+ Poly-Silicon Gate On Gate Oxide Properties</i> , 1994 IEEE, pages 107-108				
			(2 pages).				
	AS						
	AT						
EXAMINER				DATE CONSIDERED			
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